

Isc N-Channel MOSFET Transistor

SPA16N50C3

FEATURES

- Drain-source on-resistance:
 R_{DS}(on) ≤ 250mΩ@10V
- Reduced switching and conduction losses
- · 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

· Switching applications

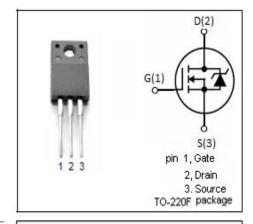


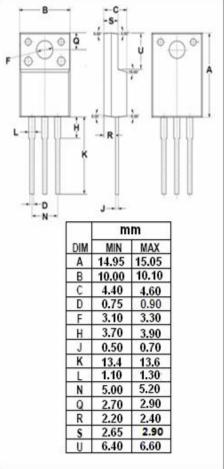
• ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{DSS}	Drain-Source Voltage	500	٧
V _{GSS}	Gate-Source Voltage	±20	V
I _D	Drain Current-Continuous @Tc=25°C (V _{GS} at 10V) Tc=100°C	16 10	Α
I _{DM}	Drain Current-Single Pulsed	48	Α
P _D	Total Dissipation @Tc=25°C	34	W
Tj	Max. Operating Junction Temperature	-55~150	$^{\circ}$
T _{stg}	Storage Temperature	-55~150	$^{\circ}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
Rth(ch-c)	Channel-to-case thermal resistance	3.7	°C/W
Rth(ch-a)	h(ch-a) Channel-to-ambient thermal resistance		°C/W







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• ELECTRICAL CHARACTERISTICS

T_c=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D =0.25mA	500			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} ; I _D =0.675A	2.1	3	3.9	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = 10V; I _D =10A		0.25	0.28	Ω
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ±20V;V _{DS} = 0V			±100	nA
I _{DSS}	Drain-Source Leakage Current	V _{DS} = 500V; V _{GS} = 0V;Tj=25°C V _{DS} =500V; V _{GS} = 0V; Tj=150°C		0.1	1 100	μА
V _{SDF}	Diode forward voltage	I _{SD} =16A, V _{GS} = 0 V		1	1.2	V

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